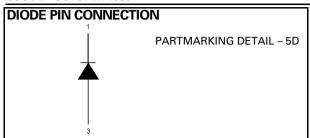
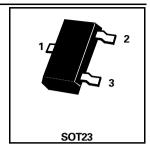
## SOT23 SILICON PLANAR HIGH SPEED SWITCHING DIODE

**FMMD914** 

**ISSUE 2 - OCTOBER 1995** 





## ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Working Peak Reverse Voltage	$V_{RWM}$	75	V
Average Rectified Forward Current at T <sub>amb</sub> =25°C	I <sub>F(AV)</sub>	75	mA
Repetitive Peak Forward Current	I <sub>FRM</sub>	225	mA
Power Dissipation at T <sub>amb</sub> = 25°C	P <sub>tot</sub>	330	mW
Operating and Storage Temperature Range	T <sub>j</sub> :T <sub>stg</sub>	-55 to +150	°C

## ELECTRICAL CHARACTERISTICS (at T<sub>amb</sub> = 25°C unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Reverse Breakdown Voltage	V <sub>BR</sub>	75		V	I <sub>R</sub> =100μA
Forward Voltage	V <sub>F</sub>		1	V	I <sub>F</sub> =10mA
Static Reverse Current	I <sub>R</sub>		25 50	nA μA	V <sub>R</sub> =20V V <sub>R</sub> =20V, T <sub>amb</sub> =150 °C
Reverse Recovery Time	t <sub>rr</sub>		8	ns	$I_F = I_{RM} = 10 \text{mA}, I_{RR} = 1 \text{mA}$ $R_L = 100 \Omega$
			4	ns	$I_{F}=10\text{mA}, I_{RR}=1\text{mA}, V_{R}=6V$ $R_{L}=100\Omega$
Total Capacitance	Ст		4	pF	V <sub>R</sub> =0, f=1MHz
Forward Recovery Voltage	V <sub>FM(REC)</sub>		2.5	V	I <sub>F</sub> =50mA, R <sub>L</sub> =50Ω
Rectification Efficiency	η <sub>r</sub>	45		%	$V_R$ =2V,R <sub>L</sub> =5k $\Omega$ , C <sub>L</sub> =20pF Z <sub>source</sub> =50 $\Omega$ , f=100MHz

Spice parameter data is available upon request for this device

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